

CMLSH-4
SURFACE MOUNT
DUAL, ISOLATED
SILICON
SCHOTTKY DIODES

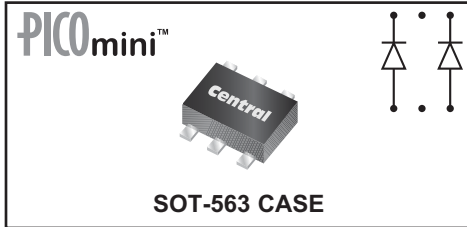


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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLSH-4 are two individual electrically isolated 40 volt Schottky Diodes, in a space saving SOT-563 surface mount package. This PICOmini™ device has been designed for applications requiring fast switching speeds and a low forward voltage drop.

MARKING CODE: C4E



MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Peak Repetitive Reverse Voltage	V_{RRM}	40	V
Continuous Forward Current	I_F	200	mA
Peak Repetitive Forward Current	I_{FRM}	350	mA
Peak Forward Surge Current, $t_p=10\text{ms}$	I_{FSM}	750	mA
Power Dissipation	P_D	250	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	Θ_{JA}	500	$^\circ\text{C/W}$

SYMBOL

UNITS

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

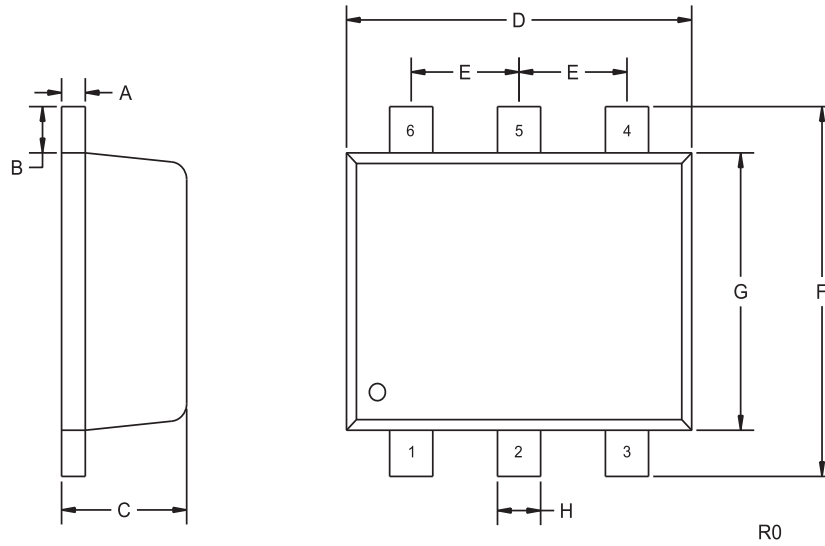
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R=25\text{V}$		90	500	nA
I_R	$V_R=25\text{V}, T_A=100^\circ\text{C}$		25	100	μA
BV_R	$I_R=100\mu\text{A}$	40	50		V
V_F	$I_F=2.0\text{mA}$		0.29	0.33	V
V_F	$I_F=15\text{mA}$		0.37	0.42	V
V_F	$I_F=100\text{mA}$		0.61	0.80	V
V_F	$I_F=200\text{mA}$		0.65	1.0	V
C_T	$V_R=1.0\text{V}, f=1.0\text{MHz}$		7.0		pF
t_{rr}	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

R1 (20-January 2010)

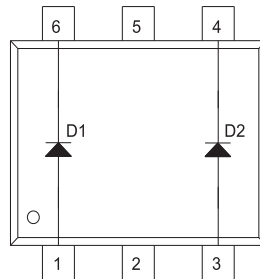
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SOT-563 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.10	0.18
B	0.008		0.20	
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.047		1.20	
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R0)

LEAD CODE:

- 1) Anode D1
- 2) NC
- 3) Anode D2
- 4) Cathode D2
- 5) NC
- 6) Cathode D1

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R1 (20-January 2010)